# International TOR Rectifier

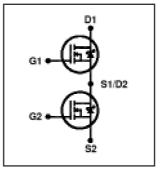
#### **DIGITAL AUDIO MOSFET**

## IRFI4212H-117P

#### **Features**

- Integrated half-bridge package
- · Reduces the part count by half
- · Facilitates better PCB layout
- Key parameters optimized for Class-D audio amplifier applications
- Low R<sub>DS(ON)</sub> for improved efficiency
- Low Qg and Qsw for better THD and improved efficiency
- Low Qrr for better THD and lower EMI
- Can delivery up to 150W per channel into  $4\Omega$  load in half-bridge configuration amplifier
- Lead-free package

Key Parameters ©				
$V_{DS}$	100	V		
R <sub>DS(ON)</sub> typ. @ 10V	58	mΩ		
Q <sub>g</sub> typ.	12	nC		
Q <sub>sw</sub> typ.	6.9	nC		
R <sub>G(int)</sub> typ.	3.4	Ω		
T <sub>J</sub> max	150	°C		





G1, G2	D1, D2	S1, S2
Gate	Drain	Source

## **Description**

This Digital Audio MosFET Half-Bridge is specifically designed for Class D audio amplifier applications. It consists of two power MosFET switches connected in half-bridge configuration. The latest process is used to achieve low on-resistance per silicon area. Furthermore, Gate charge, body-diode reverse recovery, and internal Gate resistance are optimized to improve key Class D audio amplifier performance factors such as efficiency, THD and EMI. These combine to make this Half-Bridge a highly efficient, robust and reliable device for Class D audio amplifier applications.

### **Absolute Maximum Ratings** ⑤

·	Parameter	Max.	Units	
V <sub>DS</sub>	Drain-to-Source Voltage	100	V	
$V_{GS}$	Gate-to-Source Voltage	±20		
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	11	A	
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	6.8		
DM	Pulsed Drain Current ①	44		
P <sub>D</sub> @T <sub>C</sub> = 25°C	Power Dissipation @	18	W	
P <sub>D</sub> @T <sub>C</sub> = 100°C	Power Dissipation ®	7.0		
	Linear Derating Factor	0.14	W/°C	
E <sub>AS</sub>	Single Pulse Avalanche Energy@	41	mJ	
$T_J$	Operating Junction and	-55 to + 150	°C	
T <sub>STG</sub>	Storage Temperature Range			
	Soldering Temperature, for 10 seconds	300	$\neg$	
	(1.6mm from case)			
	Mounting torque, 6-32 or M3 screw	10lb·in (1.1N·m)		

#### **Thermal Resistance** ⑤

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	Parameter	Тур.	Max.	Units		
$R_{ heta JC}$	Junction-to-Case 4		7.1	°C/W		
$R_{\theta JA}$	Junction-to-Ambient (free air)	_	65	]		

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